

# **PANIPAT INSTITUTE OF ENGINEERING & TECHNOLOGY**

## **Department of Electronics & Communication Engineering**

### **LESSON PLAN**

**Subject Name: - VLSI Technology**  
**Year: - 3<sup>rd</sup>**

**Subject Code: - ECP-5A**  
**Semester:- 5th**

<b>Lecture No</b>	<b>Unit No</b>	<b>Topic</b>	<b>References</b>
<b>L-1</b>	I	Introduction to subject, Course Outcomes, Pre-requisites, Assessments	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-2</b>	I	Crystal structure of Silicon, Polycrystalline and single crystal- Comparison	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-3</b>	I	Orientation of crystals and significance in IC fabrication	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-4</b>	I	BJTs, MOSFETs and FinFETs	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-5</b>	I	Clean Room Concept	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-6</b>	I	Si or Ge, significance in Fabrication of ICs	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-7</b>	I	Growth of single crystal Si	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-8</b>	II	Epitaxial growth process	Sze SM. VLSI technology. McGraw-hill; 1988.

<b>L-9</b>	II	VPE and MBE techniques	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-10</b>	II	Comparison of epitaxial growth processes, important parameters	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-11</b>	I	Fabrication process of p-n diode	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-12</b>	I	Oxidation – Growth mechanism	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-13</b>	I	Kinetics of oxidation	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-14</b>	I	oxidation techniques and systems	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-15</b>	I	Oxide properties	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-16</b>	I	oxide induced defects	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-17</b>	I	characterisation of oxide films,	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-18</b>	I	Use of thermal oxide and CVD oxide	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-19</b>	I	growth and properties of dry and wet oxide	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-20</b>	I	dopant distribution	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-21</b>	I	oxide quality	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-22</b>	-	Isolation Techniques with reference to VLSI circuits	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-23</b>	II	Solid State Diffusion – Fick's equation	Sze SM. VLSI technology. McGraw-hill; 1988.

<b>L-24</b>	II	atomic diffusion mechanisms	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-25</b>	II	measurement techniques	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-26</b>	II	diffusion in polysilicon and silicon di-oxide diffusion systems	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-27</b>	II	Ion implantation – Range theory	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-28</b>	II	Equipments	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-29</b>	II	annealing	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-30</b>	II	shallow junction, high energy implementation	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-31</b>	III	Mask making, E-beam writing, Lithography – Optical lithography	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-32</b>	III	Revision for Sessional	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-33</b>	III	Discussion on Sessional, Identifying students for remedial class	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-34</b>	III	Lift-off technique	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-35</b>	III	Some Advanced lithographic techniques	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-36</b>	IV	Metallisation - Different types of metallisation	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-37</b>	IV	Physical Vapour Deposition – APCVD	Sze SM. VLSI technology. McGraw-hill; 1988.

<b>L-38</b>	IV	Plasma CVD	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-39</b>	IV	MOCVD	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-40</b>	IV	Fabrication process of Schottky diodes	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-41</b>	IV	VLSI Process integration	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-42</b>	IV	NMOS fabrication process	Sze SM. VLSI technology. McGraw-hill; 1988.
<b>L-43</b>	IV	VLSI Packaging Considerations	Sze SM. VLSI technology. McGraw-hill; 1988.

**Text Books:**

- 1) Sze SM. VLSI technology. McGraw-hill; 1988.

**Reference Books:**

- 1). S. K. Gandhi, VLSI Fabrication Principles, Wiley, 2nd edition
- 2). Sedra & Smith, Microelectronic Circuits 2004, Oxford, 5th edition